TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

# TK8A50D

### **Switching Regulator Applications**

Low drain-source ON-resistance:  $R_{DS(ON)} = 0.7 \Omega$  (typ.)

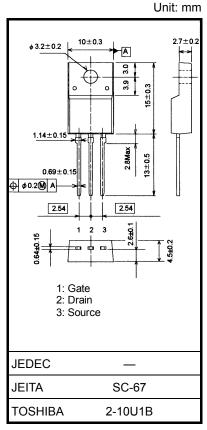
• High forward transfer admittance: |Y<sub>fs</sub>| = 4.0 S (typ.)

• Low leakage current:  $I_{DSS}$  = 10  $\mu$ A (max) ( $V_{DS}$  = 500 V)

• Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteristics                        |                              | Symbol           | Rating     | Unit |  |
|--|------------------------------|------------------|------------|------|--|
| Drain-source voltage                   |                              | $V_{DSS}$        | 500        | V    |  |
| Gate-source voltage                    |                              | V <sub>GSS</sub> | ±30        | V    |  |
| Drain current                          | DC (Note 1)                  | I <sub>D</sub>   | 8          |      |  |
|  | Pulse (t = 1 ms)<br>(Note 1) | I <sub>DP</sub>  | 32         | Α    |  |
| Drain power dissipati                  | on (Tc = 25°C)               | P <sub>D</sub>   | 40         | W    |  |
| Single pulse avalanche energy (Note 2) |                              | E <sub>AS</sub>  | 165        | mJ   |  |
| Avalanche current                      |                              | I <sub>AR</sub>  | 8          | Α    |  |
| Repetitive avalanche                   | energy (Note 3)              | E <sub>AR</sub>  | 4.0        | mJ   |  |
| Channel temperature                    |                              | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature range              |                              | T <sub>stg</sub> | -55 to 150 | °C   |  |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

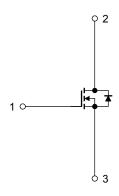
| Characteristics                        | Symbol                 | Max   | Unit |
|--|------------------------|-------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 3.125 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5  | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 4.4 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 8 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Start of commercial production 2008-07



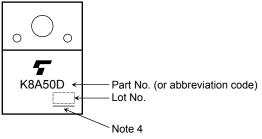
#### **Electrical Characteristics (Ta = 25°C)**

| Char                         | acteristics    | Symbol               | Test Condition  | Min | Тур. | Max  | Unit |
|------------------------------|----------------|----------------------|---|-----|------|------|------|
| Gate leakage cur             | rent           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$   | _   | _    | ±1   | μА   |
| Drain cut-off current        |                | I <sub>DSS</sub>     | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V  | _   | _    | 10   | μА   |
| Drain-source bre             | akdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 500 | _    | _    | V    |
| Gate threshold ve            | oltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA   | 2.0 | _    | 4.0  | V    |
| Drain-source ON              | -resistance    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A  |     | 0.7  | 0.85 | Ω    |
| Forward transfer             | admittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4 A  | 1.0 | 4.0  | _    | S    |
| Input capacitance            |                | C <sub>iss</sub>     |   | _   | 800  | _    | pF   |
| Reverse transfer capacitance |                | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz  | _   | 4    | _    |      |
| Output capacitance           |                | C <sub>oss</sub>     |   | _   | 100  | _    |      |
| Switching time               | Rise time      | t <sub>r</sub>       | $\begin{array}{c c} 10 \text{ V} & \text{I}_D = 4 \text{ A} & \text{V}_{\text{OUT}} \\ \hline 0 \text{ V} & \text{S} & \text{RL} = 50 \Omega \\ \hline \end{array}$ | _   | 20   | _    | - ns |
|                              | Turn-on time   | t <sub>on</sub>      |   | _   | 40   | _    |      |
|                              | Fall time      | t <sub>f</sub>       |   | _   | 12   | _    |      |
|                              | Turn-off time  | t <sub>off</sub>     | V <sub>DD</sub> ≈ 200 V<br>Duty ≤ 1%, t <sub>W</sub> = 10 μs  | _   | 60   | _    |      |
| Total gate charge            |                | Qg                   |   | _   | 16   | _    |      |
| Gate-source charge           |                | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$  | _   | 10   | _    | nC   |
| Gate-drain charge            |                | Q <sub>gd</sub>      |   | _   | 6    |      |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | $I_{DR}$         | _   | _   | _    | 8    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _   | _   | _    | 32   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | $I_{DR} = 8 \text{ A}, V_{GS} = 0 \text{ V},$ | _   | 1200 | _    | ns   |
| Reverse recovery charge                   | Qrr              | dI <sub>DR</sub> /dt = 100 A/μs               | _   | 10   | _    | μС   |

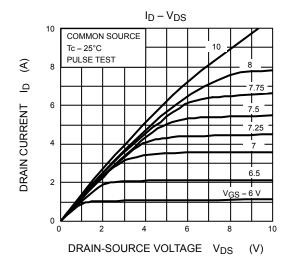
#### Marking

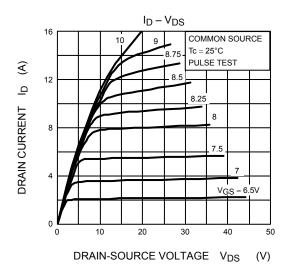


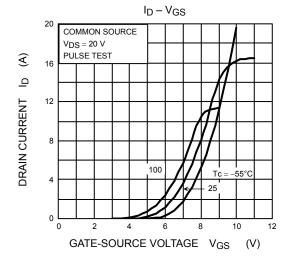
Note 4: A line under a Lot No. identifies the indication of product Labels.

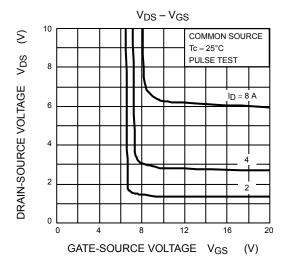
[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

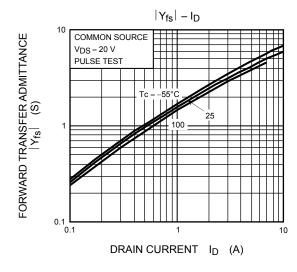
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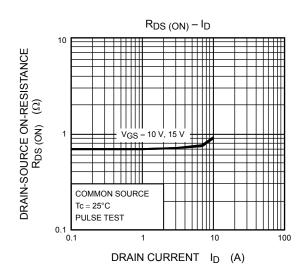


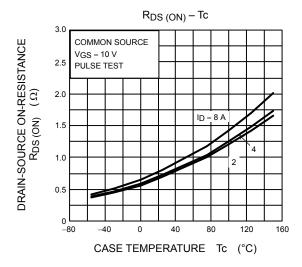


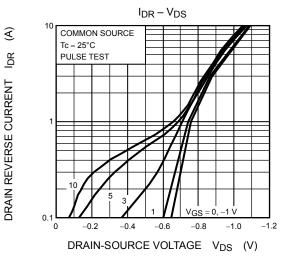


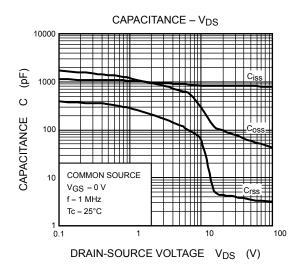


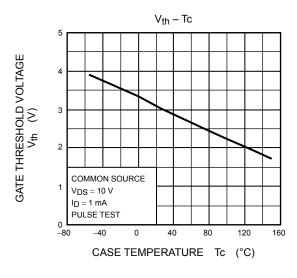


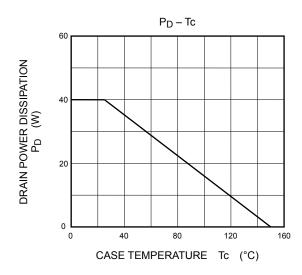


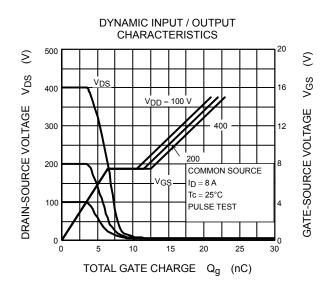


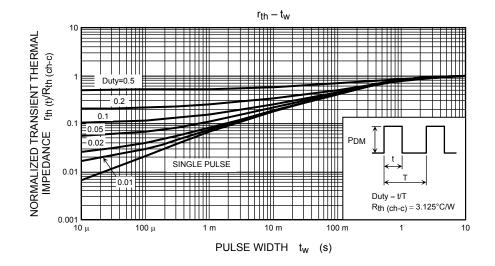


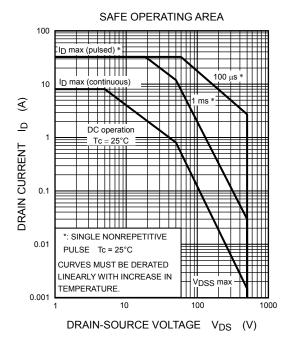


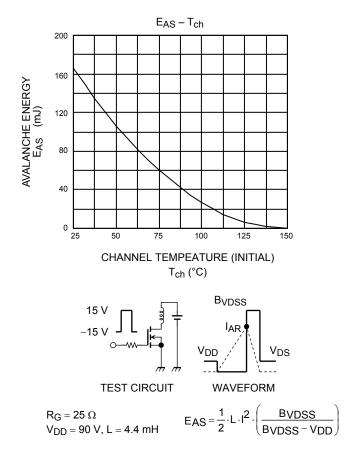












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